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: 2018.11.02

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10G 850nm DWDM CSEL LD TO-CAN Series

Features:

Da a a e 10 Gb/
850 nm DWDM
L h e h d a d e a i c e

Applications:

High speed Data Center
10Gigabit Ethernet

Specifications:

Reverse Voltage	V_R	—	5	V
Forward Current	I_F	—	12	A
MPD Reverse Voltage	V	20	—	V
MPD Forward Current	V_f	—	10	A
Operating Temperature	T	-5	+70	°C
Storage Temperature	T _g	-40	+85	°C
Lead Solder Temperature	—	—	260	°C
Lead Solder Time	—	—	10	

: (°C)

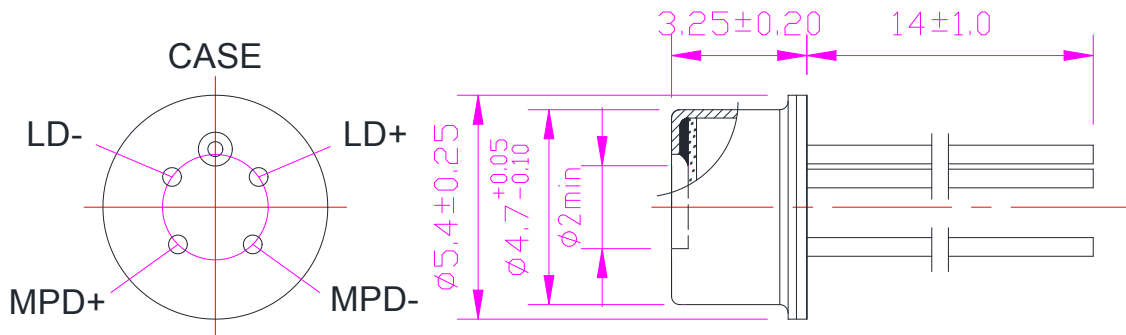
Threshold Current	I_h	T=25°C	—	0.8	1.2	A
Optical Output Power	P	I = 6.5 A	0.85	1.0	—	W
Operating Voltage	V	I = 6.5 A	—	1.9	—	V
Emission Wavelength	λ	I = 6.5 A	840	850	860	nm
Secondary Backside Heat, RMS	—	I = 6.5 A	—	—	—	W/ A
Side Efficiency	—	I = 6.5 A	0.15	0.17	—	W/ A
Differential Resistance	R_d	I = 6.5 A	—	95	—	Ω
Rise Time	—	I = 6.5 A, 20-80%	—	30	40	ps
Fall Time	f		—	40	45	ps
Micro Current (MPD)	I	I = 6.5 A, $V_R=3V$	150	—	—	μA



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Da k C e (MPD)	Id	P c=0 W, V _R =3V	—	—	20	A
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Mechanical Dimension and Pin Assignment:



BOTTOM VIEW

Order Information:

LD 850nm VCSEL

Da a a e :
10Gb/

Heade T e:
TO46

N be fPi :
5 i

Ca T e:
FW: Fa Wi d

SAN-U he a h i f fa i f ai c ai edi hi d c
bjec cha ge ih e i f ai a bai edi a ic a e i d
SA ibe ne ef a ce f he c e ac a ea i ge i e . A
i ai ed i f he e ' efe e ce a d ha be c ide ed a a a ed
ch i SAN-U i be iab ef da age a i i g di ec i di ec hich f a e f
he i edi hi d c e .

Add e : N501-505 Wei e ee i g Pa k F O e ea Chi e e

F jia , Chi a

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[h :// www.a-c.com](http://www.a-c.com)